

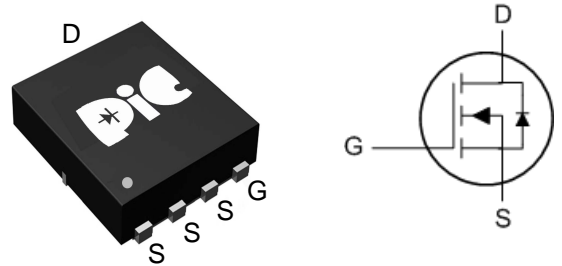
## ➤ General Description

This PAN30TY04Y N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

## ➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent  $CdV/dt$  effect decline
- Advanced high cell density Trench technology

## ➤ DFN5X6A-EP1



## ➤ Application

- DC/DC Primary Side Switch
- Industrial Synchronous
- Rectification Load Switch
- DC/DC Converters

## ➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_C=25^\circ C$	58	A
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_C=100^\circ C$	38	A
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_A=25^\circ C$	12	A
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_A=70^\circ C$	9.6	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	115	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	57.8	mJ
Avalanche Current	$I_{AS}$	34	A
Total Power Dissipation <sup>4</sup>	$P_D@T_C=25^\circ C$	46	W
Total Power Dissipation <sup>4</sup>	$P_D@T_A=25^\circ C$	2	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^\circ C$
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	62	$^\circ C/W$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	2.7	$^\circ C/W$

### ➤ Electrical Characteristics (T<sub>J</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
BVDSS Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Reference to 25°C, I <sub>D</sub> =1mA	---	0.027	---	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	6.5	8.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	11	14	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.5	2.5	V
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub>		---	-5.8	---	mV/°C
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	---	38	---	S
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.7	2.9	Ω
Total Gate Charge (4.5V)	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	12.6	17.6	nC
Gate-Source Charge	Q <sub>gs</sub>		---	4.2	5.9	
Gate-Drain Charge	Q <sub>gd</sub>		---	5.1	7.1	
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =15A	---	4.6	9.2	ns
Rise Time	T <sub>r</sub>		---	12.2	22	
Turn-Off Delay Time	T <sub>d(off)</sub>		---	26.6	53	
Fall Time	T <sub>f</sub>		---	8	16	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	1317	1844	pF
Output Capacitance	C <sub>oss</sub>		---	163	228	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	131	183	

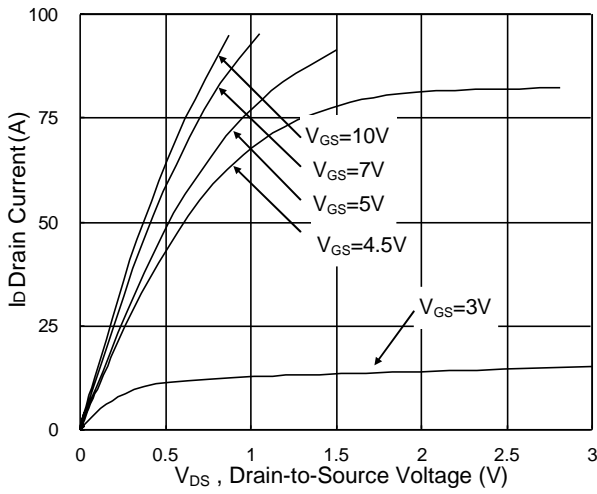
### ➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current <sup>1,5</sup>	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	58	A
Pulsed Source Current <sup>2,5</sup>	I <sub>SM</sub>		---	---	115	A
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =30A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	9.2	---	nS
Reverse Recovery Charge	Q <sub>rr</sub>		---	2	---	nC

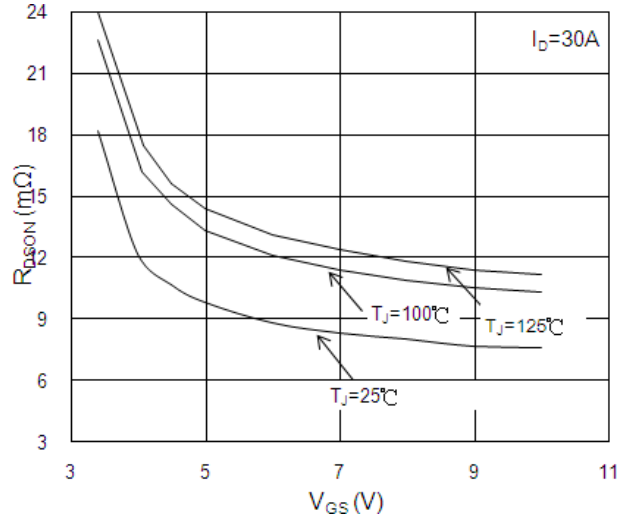
Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=34A
4. Ensure that the channel temperature does not exceed 150°C.
5. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

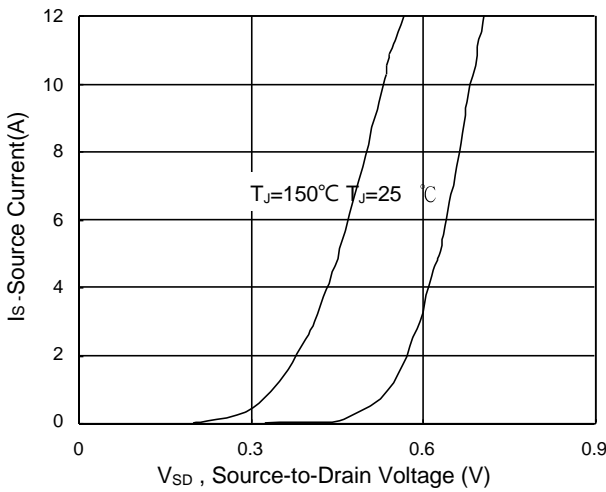
## ➤ Typical Characteristics



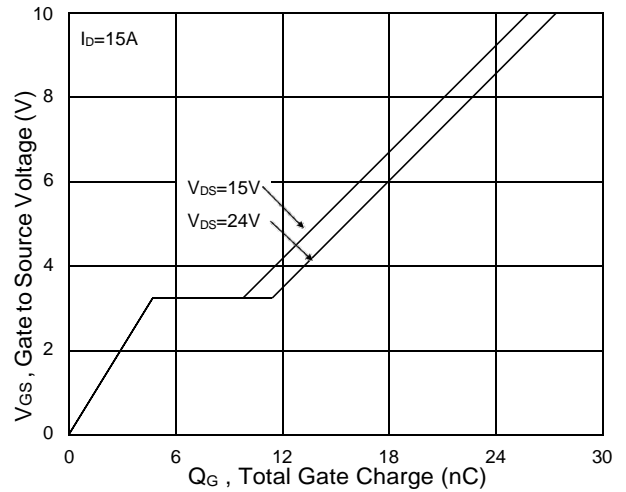
**Fig.1 Typical Output Characteristics**



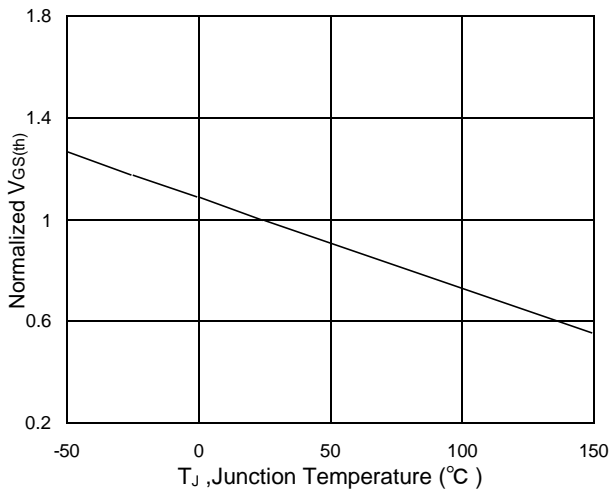
**Fig.2 On-Resistance vs. Gate-Source**



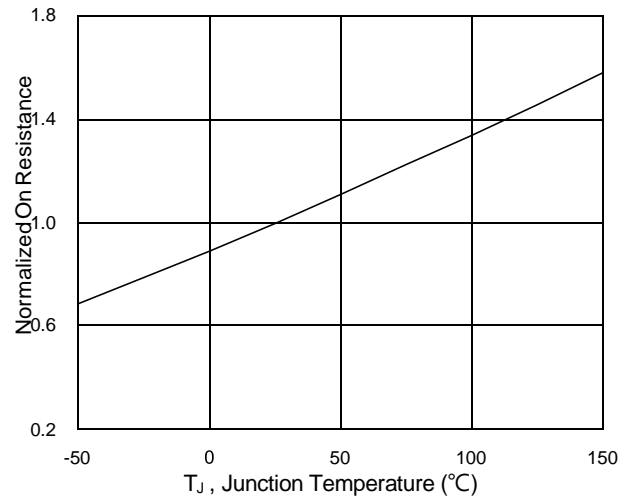
**Fig.3 Forward Characteristics of reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(ON)}$  vs.  $T_J$**

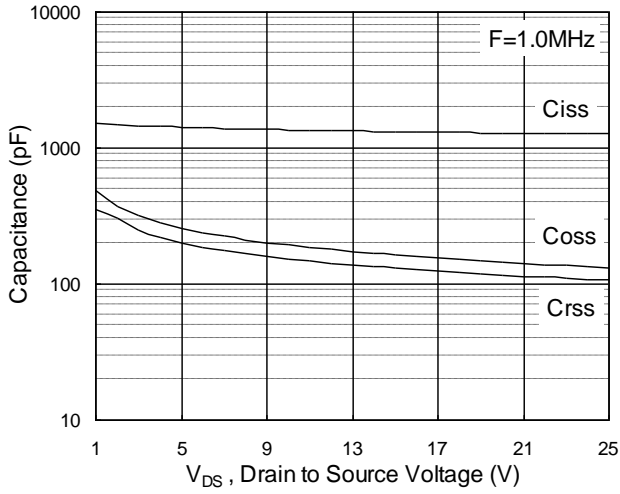


Fig.7 Capacitance

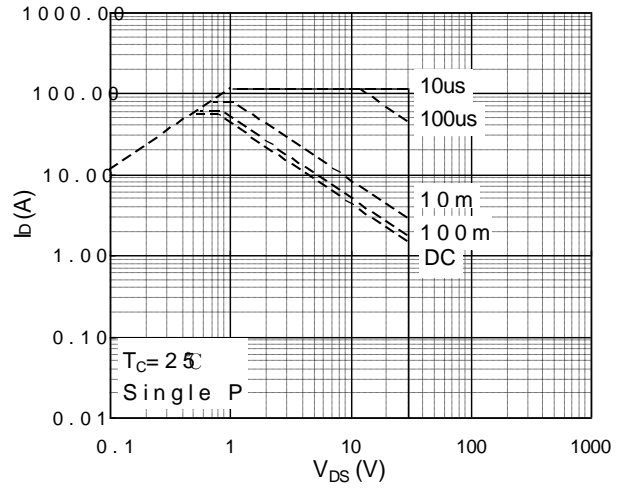


Fig.8 Safe Operating Area

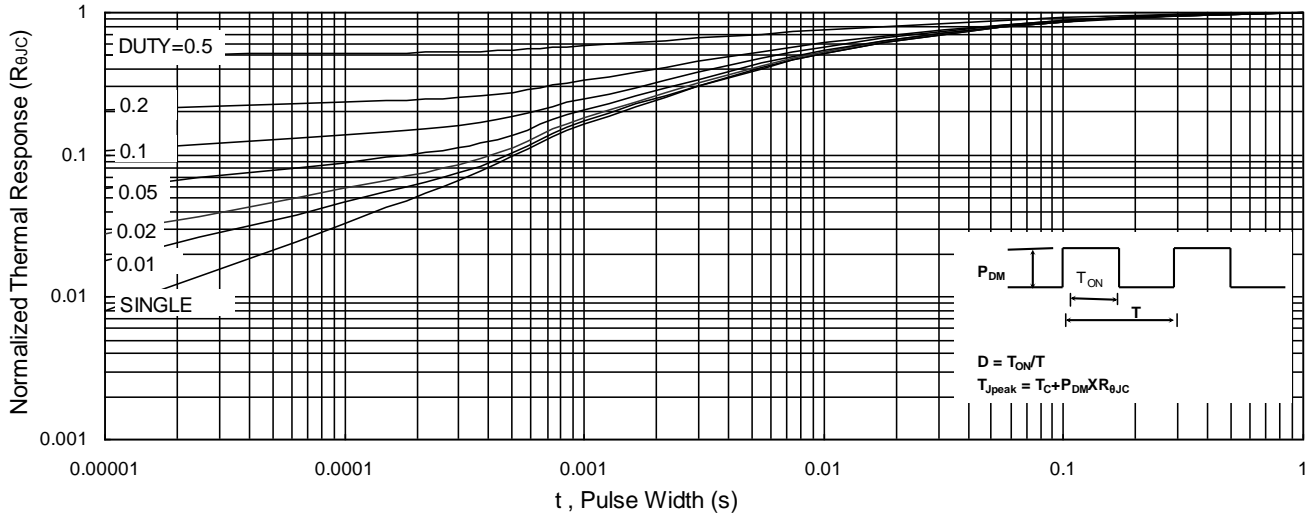


Fig.9 Normalized Maximum Transient Thermal Impedance

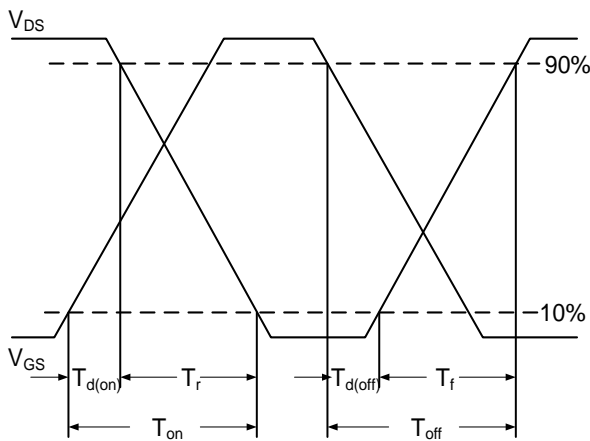


Fig.10 Switching Time Waveform

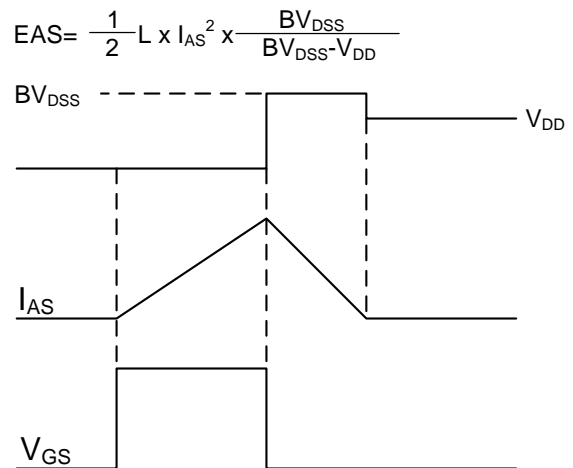
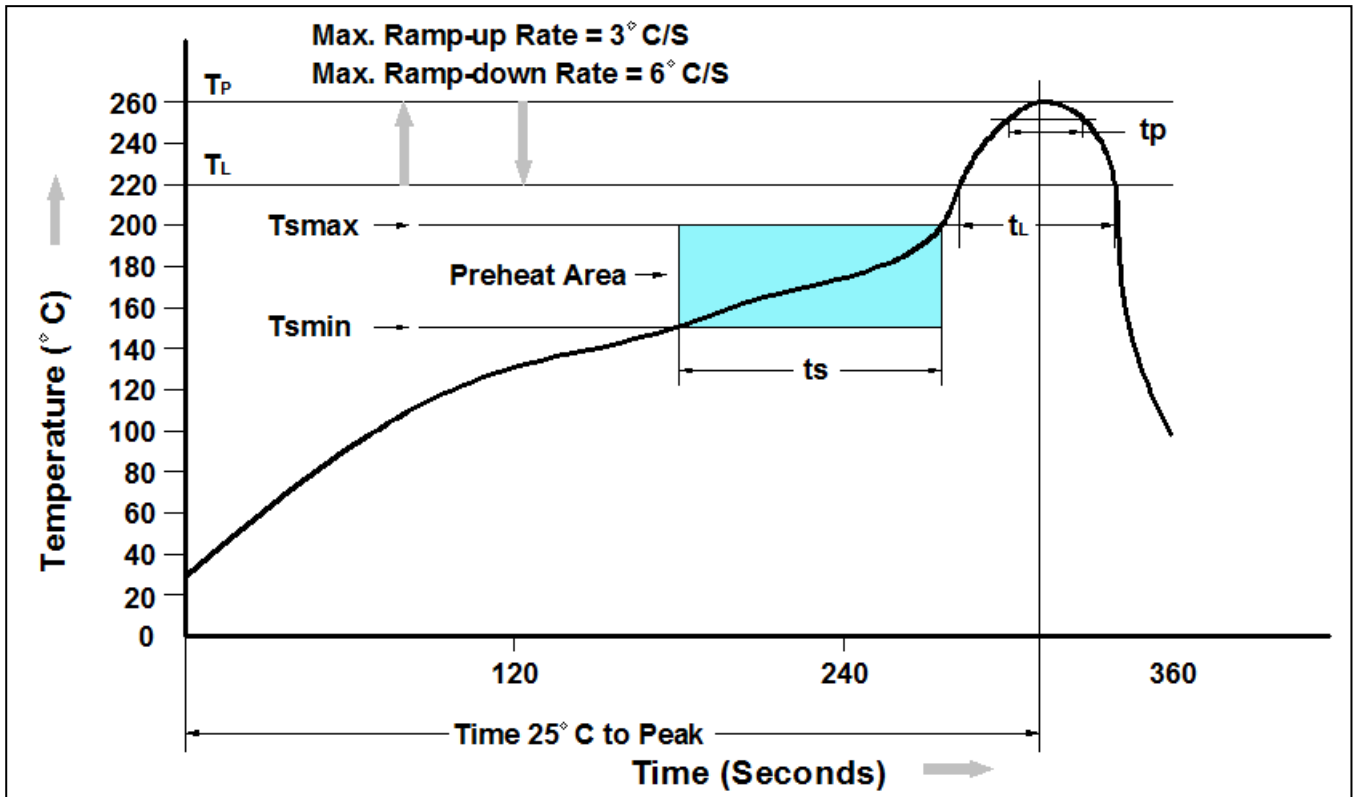


Fig.17 Unclamped Inductive Switching Waveform

➤ Recommend IR Reflow Soldering Thermal Profile

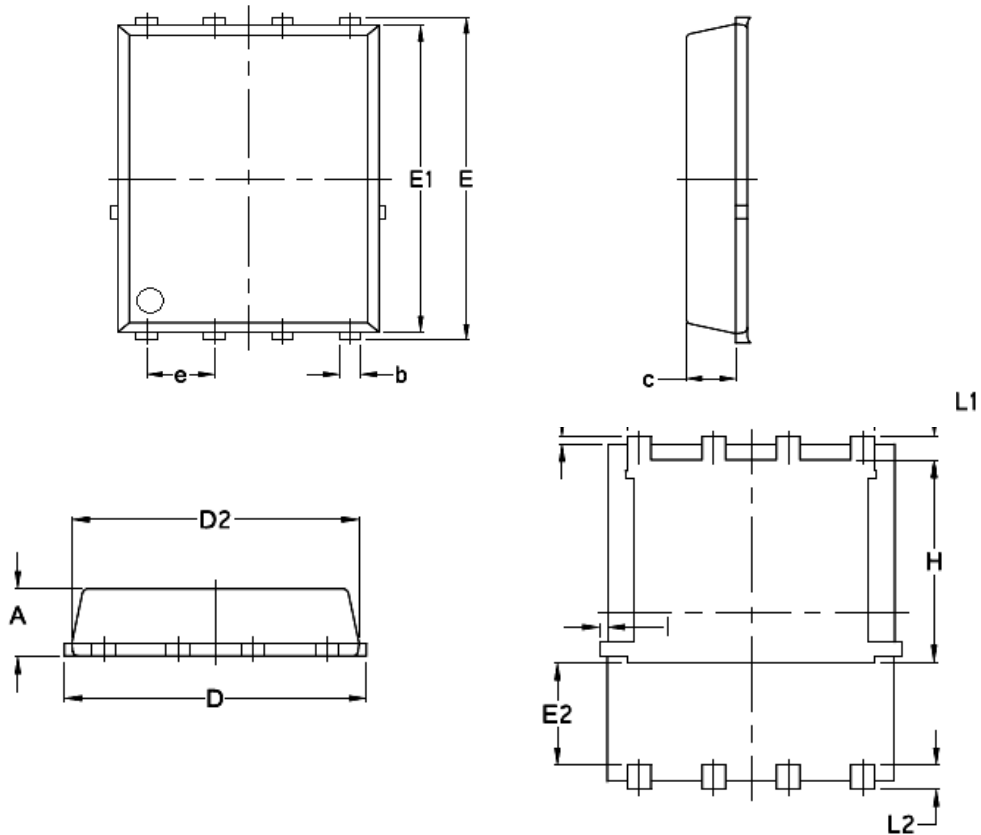


Profile Feature	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	150°C
Temperature Max. ( $T_{smax}$ )	200°C
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds
Average Ramp-up Rate ( $t_L$ to $t_P$ )	3°C/second max.
Liquidous Temperature ( $T_L$ )	217°C
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time ( $t_P$ ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN30TY04Y	DFN5X6A-EP1 Reel	3000 pcs

➤ Package Information ( DFN5X6A EP1 )



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
I	---	0.18	---	0.0070
E	5.90	6.15	0.2323	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.10	---	0.0433	---
e	1.27 BSC		0.05 BSC	
H	3.30	3.78	0.1299	0.1488
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.61	0.0150	0.0240
L2	0.38	0.71	0.0150	0.0279

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